Ingo Tischer

List of Publications by Year in descending order

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1163117 1058476 29 215 8 14 citations h-index g-index papers 29 29 29 321 times ranked docs citations citing authors all docs

#	Article	IF	CITATIONS
1	<mml:math display="inline" xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mrow><mml:mn></mml:mn></mml:mrow></mml:mrow></mml:math>	w&⊈mml:	ന ങ് ൾ>
2	Cathodoluminescence of GalnN quantum wells grown on nonpolar a plane GaN: Intense emission from pit facets. Applied Physics Letters, 2010, 97, 101904.	3.3	14
3	Determination of axial and lateral exciton diffusion length in GaN by electron energy dependent cathodoluminescence. Journal of Applied Physics, 2016, 120, .	2.5	14
4	Cathodoluminescence and photoluminescence study on AlGaN layers grown with SiNx interlayers. Applied Physics Letters, 2010, 97, .	3.3	12
5	Stacking faultâ€related luminescence features in semiâ€polar GaN. Physica Status Solidi (B): Basic Research, 2011, 248, 611-615.	1.5	12
6	Three-dimensional reciprocal space mapping of diffuse scattering for the study of stacking faults in semipolar (f 11{overline 2}2) GaN layers grown from the sidewall of an <i>r</i> -patterned sapphire substrate. Journal of Applied Crystallography, 2013, 46, 1425-1433.	4.5	11
7	Optical gas sensing by micro-photoluminescence on multiple and single ZnO nanowires. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1810-1816.	1.8	11
8	Light-emitting diode based on mask- and catalyst-free grown N-polar GaN nanorods. Nanotechnology, 2011, 22, 265202.	2.6	9
9	Structural and cathodoluminescence properties of ZnO nanorods after Ga-implantation and annealing. Journal of Applied Physics, 2009, 105 , .	2.5	8
10	Nanoscale characterisation of semiconductors by cathodoluminescence. IOP Conference Series: Materials Science and Engineering, 2014, 55, 012018.	0.6	8
11	Semipolar GalnN quantum well structures on large area substrates. Physica Status Solidi (B): Basic Research, 2012, 249, 464-467.	1.5	7
12	EBIC investigations on polar and semipolar InGaN LED structures. Physica Status Solidi (B): Basic Research, 2016, 253, 126-132.	1.5	7
13	Studies on Defect Reduction in AlGaN Heterostructures by Integrating an In-situ SiN Interlayer. Japanese Journal of Applied Physics, 2013, 52, 08JJ07.	1.5	6
14	GaN tubes with coaxial non―and semipolar GalnN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 648-651.	0.8	6
15	Luminescence properties of epitaxially grown GaN and InGaN layers around ZnO nanopillars. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1582-1585.	1.8	5
16	Catalytic growth of hexagonally aligned ZnO nanorods. Physica Status Solidi (B): Basic Research, 2011, 248, 1915-1918.	1.5	5
17	Basal plane stacking faults in semipolar AlGaN: Hints to Al redistribution. Physica Status Solidi (B): Basic Research, 2014, 251, 2321-2325.	1.5	5
18	Optical properties of defects in nitride semiconductors. Journal of Materials Research, 2015, 30, 2977-2990.	2.6	5

#	Article	lF	CITATIONS
19	Stacking fault emission in GaN: Influence of n-type doping. Journal of Applied Physics, 2016, 119, .	2.5	5
20	Three-dimensional cathodoluminescence characterization of a semipolar GalnN based LED sample. Journal of Applied Physics, 2017, 121, .	2.5	5
21	Evidence of terbium and oxygen co-segregation in annealed AlN:Tb. Applied Physics Letters, 2017, 110, .	3.3	5
22	INGAN/GAN based semipolar green converters. Journal of Crystal Growth, 2013, 370, 120-123.	1.5	3
23	Coaxial InGaN epitaxy around GaN micro-tubes: Tracing the signs. Journal of Crystal Growth, 2013, 370, 319-322.	1.5	3
24	Suppression of gallium inhomogeneity in ZnO nanostructures on GaN using seed layers. Materials Letters, 2012, 83, 31-34.	2.6	1
25	Optical Properties of ZnO/GaN/InGaN Core–Shell Nanorods. Japanese Journal of Applied Physics, 2013, 52, 075201.	1.5	1
26	Measurement of the diffusion length and the lifetime of free excitons in gallium nitride using cathodoluminescence under different conditions of luminescence excitation. Journal of Surface Investigation, 2015, 9, 839-843.	0.5	1
27	Crystal quality improvement of semipolar (20-21) GaN on patterned sapphire substrates by in-situ deposited SiN mask., 2014,,.		O
28	(Invited) Large Area Semipolar GaN Grown on Foreign Substrates. ECS Transactions, 2014, 61, 101-107.	0.5	0
29	Composition analysis of coaxially grown InGaN multi quantum wells using scanning transmission electron microscopy. Journal of Applied Physics, 2016, 119, 175701.	2.5	O